A Power Efficient Gain Enhancing Technique for Current Mirror

T. Azadmousavi*, H. Faraji Baghtash*(C.A.) and E. Najafi Aghdam*

Abstract: This work introduces a new and simple method for adjusting the gain of current mirror. The major advantage of the proposed architecture is that, unlike the conventional variable gain current mirror, it does not need the change of the biasing current to adjust current gain. Therefore, the power dissipation remains constant in all of the gain settings. In addition, the proposed variable gain current mirror have linear-in-dB gain control characteristic, simple structure, and small occupied area. The gain of the current mirror can be simply varied from 1.3dB to 21dB while the 3-dB bandwidth of the circuit remains around 12.3MHz or 33.6MHz at operation frequency range of 1.9MHz-14.2MHz and 6.6MHz-40.2MHz respectively. The proposed circuit draws negligible power of 6.9µW from 1.8V supply voltage. The simulation results of designed variable gain current mirror in 0.18μm standard CMOS technology confirms the effectiveness of the proposed circuit.

Keywords: Variable Gain Current Mirror, Constant Power Consumption, Relocating Pole-Zero, Linear-in-dB.

1 Introduction

In the recent years, using current mode signal processing has received significant attention due to the low-power operation, wide dynamic range, high frequency operation and simple structure [1-4]. One of the most important and widely used building blocks of current mode signal processing is variable gain current mirror (VGCM). For instance, it is commonly used in applications such as tunable filters and adjustable gain amplifiers. It also find its application in circuits designed for biomedical applications [5-8]. So far, various techniques introduced to control the current gain of current mirrors [9-11]. Currently, the research on tunable current mirrors are mainly focused on the reduction power consumption and increment of gain tuning range, and operating speed [12-15]. For instance, the power consumption in [12] has been decreased, however, its tuning range and frequency bandwidth are very limited. On the other hand, [13] can deliver wide tuning range and frequency bandwidth, but it has a relatively high power consumption that is not suitable for ultra-low power applications. In all of these circuits, the operating current or voltage of circuit is varied to adjust the gain. As a result, the power consumption will be different at various gain settings. This, however, may not suitable for specific high performance applications that require ultra-low and constant power consumption.

In this work, a new low power, linear-in-dB VGCM structure is introduced which delivers constant power consumption profile all-over the gain range. The proposed technique enables the structure to deliver some ever interesting features of low power consumption, wide programmable gain range, and acceptable frequency bandwidth. The paper is organized in four subsequent sections. The structure of proposed VGCM is described in Section 2. In the next section, simulation results using 0.18μm standard CMOS technology is presented. Finally, Section 4 concludes this work.

2 Proposed Circuit

2.1 Operational Principle

The conceptual schematic of the gain adjusting
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2.2 Transistor level implementation of proposed VGCM

Figure 4 shows a current mirror with constant gain of \(I_1/I_2\). In this circuit, the \(M_1\) and \(M_2\) form a source follower voltage buffer as well as \(M_2\) and \(M_9\) do. Through these two voltage followers, the gates of \(M_3\) and \(M_4\) follow the voltage of input node, constructing a current mirror circuit. There is an interesting feature with this structure, that is the capability of separately setting the gate voltage of \(M_1\) and \(M_9\) and consequently the mirroring ratio of current mirror by simply adjusting \(I_1\) and \(I_2\) (see Fig. 4). Transistors \(M_{2-6}\) are cascode transistors which used to enhance the gain accuracy of current mirror. In order to add variable gain capability to the proposed CM, two adjustable capacitors are applied to the gate-drain nodes of \(M_1\) and \(M_9\). The final schematic of proposed VGCM is shown in Fig. 5. The proposed VGCM has two main poles and one zero. The capacitors \(C_1\) and \(C_2\) determine \(Z_1\), \(P_1\) and \(P_2\), respectively. By selecting the appropriate amount for \(C_1\) and \(C_2\), the zero can be located at lower frequencies compared to the poles. Therefore, as described in previous section, the gain of the VGCM can be changed by relocating either zero and second pole or first pole.

3 Simulation Results

The proposed structure is simulated in TSMC 0.18\(\mu\)m standard CMOS technology. As the two versions of proposed VGCM (CZ-VGCM, AZ-VGCM) find very different applications, thus we examined the performance of each structure at different operating frequencies.

Therefore, in the circuit of CZ-VGCM, \(C_1\) is 29fF and \(C_2\) varied from 6fF to 96fF and for AZ-VGCM, \(C_2\) is 29fF and \(C_1\) varied from 8fF to 128fF. Fig. 6 shows the frequency response of the CZ-VGCM and AZ-VGCM at various gain settings. Fig. 6 (a) illustrates that the
current gain can be changed from 1.3dB to 21dB by varying of $C_2$, while its 3-dB bandwidth well-remains constant around 33.6MHz. Also, by changing of $C_1$ the current gain of the AZ-VGCM ranges from 1.8dB to 21.6dB while its 3-dB bandwidth remains around 12.3MHz.

The Monte-Carlo simulation are done on the threshold voltage of the CZ-VGCM in the case of $C_1$ is 6fF. The results are depicted in Fig. 7 and it shows that for the 15mv deviation of threshold voltage, the gain of the CZ-VGCM varied only 2.4dB. The current gain versus capacitor for CZ-VGCM and AZ-VGCM are plotted in Fig. 8, illustrating the linear-in-dB characteristic of the proposed structure.

The Power Consumption versus different capacitors of the proposed CZ-VGCM is shown in Fig. 9 and it validated the constant power consumption during the gain settings.

The input referred noise characteristic of the both VGCMs are shown in Fig.10, demonstrating very low input referred noise. Fig.10 (a) represents that the input referred noise value well remains less than 1.1pA/√Hz all over the interested frequency bandwidth for CZ-VGCM. Also as shown in Fig.10 (b), the input referred noise value of the AZ-VGCM at its entire frequency bandwidth is evaluated to be less than 5.2pA/√Hz. The layout of the proposed VGCM is shown in Fig. 11 and the occupied area is 58 x 20 μm².

Table 1 compares performance of the two versions of VGCM with Pre-Layout and Post-Layout simulation results. It demonstrates that AZ-VGCM is appropriate choice for applications which their operation frequency falls at 1.9MHz-14.2MHz range. On the other hand, for applications with operation frequency range from 6.6MHz to 40.2MHz, CZ-VGCM would be a good candidate. The transistors aspect ratios are given in Table 2. The performance compassion between the proposed VGCM (CZ-VGCM) and some other published works is reported in Table 3.
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Fig. 8 The dB-linearity characteristic a) CZ-VGCM and b) AZ-VGCM.

Fig. 9 The Power Consumption versus different capacitors.

Fig. 10 The input referred noise as a function of frequency a) CZ-VGCM and b) AZ-VGCM.

Fig. 11 The layout of the proposed CZ and AZ VGCM.

Table 1 Comparison between two methods of tuning gain.

<table>
<thead>
<tr>
<th></th>
<th>( C_1 ) (fF)</th>
<th>( C_2 ) (fF)</th>
<th>Gain range (dB)</th>
<th>Bandwidth 3-dB (MHz)</th>
<th>Frequency Operation (MHz)</th>
<th>Input Referred Noise (IRN) pA/( \sqrt{\text{Hz}} )</th>
</tr>
</thead>
<tbody>
<tr>
<td>CZ-VGCMa</td>
<td>29</td>
<td>6-96</td>
<td>0-20.7</td>
<td>45</td>
<td>6.46-51.5</td>
<td>&lt; 1</td>
</tr>
<tr>
<td>CZ-VGCMb</td>
<td>29</td>
<td>6-96</td>
<td>1.3-21</td>
<td>33.6</td>
<td>6.6-40.2</td>
<td>&lt; 1.1</td>
</tr>
<tr>
<td>AZ-VGCMa</td>
<td>8-128</td>
<td>29</td>
<td>0-21</td>
<td>12</td>
<td>1.77-13.8</td>
<td>&lt; 5</td>
</tr>
<tr>
<td>AZ-VGCMb</td>
<td>8-128</td>
<td>29</td>
<td>1.8-21.6</td>
<td>12.3</td>
<td>1.9-14.2</td>
<td>&lt; 5.2</td>
</tr>
</tbody>
</table>
Table 2 Transistors aspect ratios.

<table>
<thead>
<tr>
<th>Transistor</th>
<th>W/L (μm/μm)</th>
</tr>
</thead>
<tbody>
<tr>
<td>M1, M2, M3, M4, M5, M7</td>
<td>0.4/0.18</td>
</tr>
<tr>
<td>M6</td>
<td>5××2/0.18</td>
</tr>
</tbody>
</table>

Table 3 Performance Comparison.

<table>
<thead>
<tr>
<th>Works</th>
<th>CMOS Process (μm)</th>
<th>Power Consumption (µW)</th>
<th>Supply Voltage (V)</th>
<th>3-dB Bandwidth (MHz)</th>
<th>Gain range (dB)</th>
<th>IRN (pA/µHz)</th>
</tr>
</thead>
<tbody>
<tr>
<td>[12]</td>
<td>0.18</td>
<td>0.35</td>
<td>1.5</td>
<td>1.708</td>
<td>-1.9 to 1.58</td>
<td>-</td>
</tr>
<tr>
<td>[13]</td>
<td>0.18</td>
<td>0.72</td>
<td>1.5</td>
<td>1.708</td>
<td>-1.9 to 1.58</td>
<td>-</td>
</tr>
<tr>
<td>[14]</td>
<td>0.18</td>
<td>0.97</td>
<td>2.0</td>
<td>1.708</td>
<td>-1.9 to 1.58</td>
<td>-</td>
</tr>
<tr>
<td>[15]</td>
<td>0.18</td>
<td>1.05</td>
<td>2.0</td>
<td>1.708</td>
<td>-1.9 to 1.58</td>
<td>-</td>
</tr>
<tr>
<td>This work</td>
<td>0.18</td>
<td>0.237</td>
<td>1.5</td>
<td>1.708</td>
<td>-1.9 to 1.58</td>
<td>0.43</td>
</tr>
</tbody>
</table>

* Number of Fingers

4 Conclusion

In this paper a power efficient current gain adjustment technique is described. The operating principle of proposed structure is discussed. The proposed structure majorly enjoys from very low and constant power consumption all over the entire gain range. The proposed structure draws only 6.9µW from 1.8V power supply. Interestingly, the gain varies linear-in-dB with control signal and the structure presents constant bandwidth characteristic, both of which are very interesting parameters in variable gain structures. Simulation results in TSMC 0.18µm standard CMOS technology, confirm the proper function of the proposed design.

References


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T. Azadmousavi was born in Urmia, Iran, in 1989. She received her B.Sc. degree in Electronic Engineering from Urmia University, Urmia, Iran in 2011. Immediately after that, she started her M.Sc. studies in Microelectronic Research Laboratory at Urmia University. She is currently Ph.D. student of Electronic Engineering at Sahand University of Technology. Her current research interests include, low power analog and digital integrated circuit, wireless RFIC design and frequency synthesizer.

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